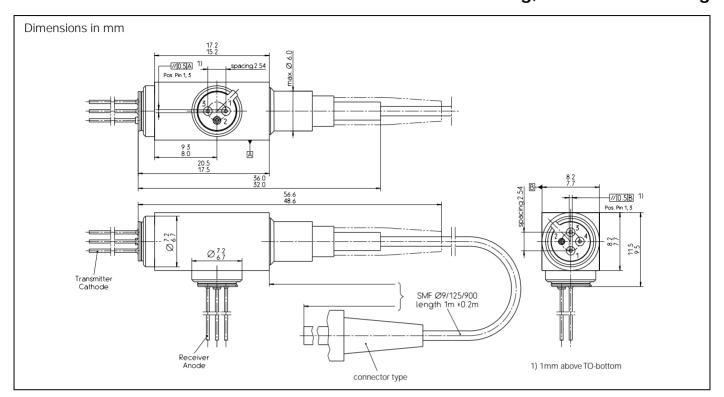


LOW POWER SBL52414x BIDI® Optical Standard Module 1310 nm Emitting, 1550 nm Receiving





FEATURES

- Designed for application in passive-optical networks
- Integrated Wavelength Division Multiplexer (WDM)
- Bi-Directional Transmission in 2nd and 3rd optical window
- · Single fiber solution
- FP-Laser Diode with Multi-Quantum Well structure
- · Class 3B Laser Product
- Suitable for bit rates up to 1.25 Gbit/s
- Ternary Photodiode at rear mirror for monitoring and control of radiant power
- Low noise / high bandwidth PIN diode
- · Hermetically sealed subcomponents, similar to TO 46
- · With singlemode fiber pigtail

Absolute Maximum Ratings

Module

Operating temperature range at case, T_C 40°C to 85°C Storage temperature range, T_{stg} 40°C to 85°C Soldering temperature t_{max} =10 s,
2 mm distance from bottom edge of case, T_S 260°C
Monitor Diode Reverse Voltage, V _R
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BIDI® is a registered trademark of Infineon Technologies
Fiber Optics

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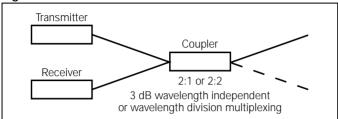
DESCRIPTION

The Infineon module for bidirectional optical transmission has been designed for different optical networks structures:

In the last few years the structure has changed from point to point planned for Broad band ISDN to a point to multipoint passive optical network (PON) architecture for the optical network in the subscriber loop.

A transceiver can be realized with discrete elements (Fig. 1). Transmitter and receiver with pigtails are connected with a fiber-coupler (2:1 or 2:2, wavelength independent or WDM).

Figure 1. Realization with discrete elements

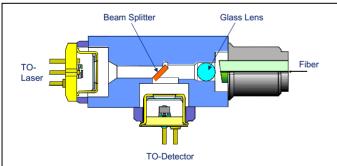


Infineon has realized this transceiver configuration in a compact module called a BIDI® (Fig. 2).

This module is especially suitable for separating the opposing signals at the ends of a link. It replaces a discrete solution with a transmitter, receiver and coupler.

The basic devices are a laser diode and a photodiode, each in a TO package, plus the filter in the beam path. A lens in the TO laser concentrates the light and enables it to be launched into the single-mode fiber of the module. In the same way the light from the fiber is focused onto the small, light-sensitive area of the photodiode to produce a high photo current. The mirror for coupling out the received signal is arranged in the beam so that the transmitter and receiver are at right angles to each other. This means the greatest possible degree of freedom in the layout of the electric circuit.

Figure 2. Compact realization of the transceiver in one module



A decisive advantage of the module is its use of standard TO components. These devices, produced in large quantities, are hermetically sealed and tested before they are built in. This makes a very substantial contribution to the excellent reliability of the module. The solid metal package of the module serves the same purpose. It allows the use of modern laser welding techniques for reliable fixing of the different elements and the fiber holder.

TECHNICAL DATA

The electro-optical characteristics described in the following tables are only valid for use within the specified maximum ratings or under the recommended operating conditions.

Transmitter Electro-Optical Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Units
Optical output power (maximum)	P _{F, max}	0.4			mW
Emission wavelength center of range P _F =0.5 P _F , max.	λ _{trans}	1270		1350	nm
Spectral width (RMS)	σ_{λ}			5	
Temperature coefficient of wavelength	TC			0.5	nm/K
Threshold current (whole temperature range)	I _{th}	2		45	mA
Forward voltage P _F =0.5 P _{F, max.}	V _F			1.5	V
Radiant power at Ith	P _{th}			20	μW
Slope efficiency (-4085°C)	η	8		60	mW/ A
Variation of 1st derivative of P/I (0.05 to 0.4 mW)	S _{var}	-30		30	%
Differential series resistance	R _S			8	Ω
Rise time (10%-90%)	t _r		100	200	ps
Fall time (10%-90%)	t _f		270	500	

Monitor Diode Electro-Optical Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Units
Dark current, V _R =5 V, P _F =0, T=T _{max}	I _R			200	nA
Photocurrent, V _R =5 V, P _F =0.5 P _F , max.	l _P	50		1500	μΑ
Capacitance, V _R =5 V, f=1 MHz	C ₅			10	pF
Tracking error ⁽¹⁾ , V _R =5 V	TE	-1		1	dB

Note

 The tracking error TE is the maximum deviation of P_F at constant current I_{mon} over a specified temperature range and relative to the reference point: I_{mon,ref}=I_{mon} (T=25°C, P_F=0.5 P_F, max.). Thus, TE is given by:

TE [dB] =
$$10 \times \log \frac{P_F [Tc]}{P_E [25^{\circ}C]}$$

Receiver Diode Electro-Optical Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Units
Spectral sensitivity $V_R=5 \text{ V}, \lambda=1550 \text{ nm}$	S _{rec}	0.65		1	A/W
Rise and fall time (10%–90%) $R_L=50 \Omega$, $V_R=5 V$	t _r ; t _f			1	ns
Total capacitance V _R =5 V, P _{opt} =0, f=1 MHz	С			1.5	pF
Dark current V _R =5 V, P _{opt} =0	I _D			50	nA

Module Electro-Optical Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Units
Optical Crosstalk ⁽¹⁾	CRT			-47	dB

Note

1. Optical Crosstalk is defined as

CRT [dB] = 10 x log
$$\frac{I_{Det.0}}{I_{Det.1}}$$

with

 $I_{Det,0}$: the photocurrent with $P_F{=}0.5~P_{F,~max.}$, without optical input, CW laser operation, $V_R{=}2~V$ and

 $I_{Det,1}$: the photocurrent without P_F but 0.5 $P_{F, max.}$ optical input

power, λ =1550 nm.

End of Life Time Characteristics

Parameter	Symbol	Min.	Тур.	Max.	Units
Threshold current at T=T _{max}	I _{th}			60	mA
Current above threshold, over full temperature range, at Imon,ref=Imon (T=25°C, P _F =0.5 P _F , max., BOL)	ΔI _F	7		70	
Tracking Error	TE	-1.5		1.5	dB
Detector Dark Current, V _R =2 V, T=T _{max}	I _R			400	nA
Monitor Dark Current, V _R =2 V, T=T _{max}	I _R			1	μΑ

FIBER DATA

The mechanical fiber characteristics are described in the following table.

Fiber Characteristics

Parameter	Min.	Тур.	Max.	Units
Mode Field Diameter	8	9	10	μm
Cladding Diameter	123	125	127	
Mode Field/Cladding Concentricity Error			1	
Cladding Non-circularity			2	%
Mode Field Non-circularity			6	
Cut off Wavelength	1270			nm
Jacket Diameter	0.8		1	mm
Bending Radius	30			
Tensile Strength Fiber Case	5			N
Length	0.8		1.2	m

Pin Description

Pinning (bottom view)	Pin Description	
ransmitter		
2.54 mm - 1	Pinning 1 (on request) LD 1 Pinning 2 (Standard) MD 4	
eceiver		
2.54 mm —► ◀—	Pinning 1 (Standard)	

Pinning 1 (Standard) 2.54 mm Pinning 1 (Standard) 2.54 mm Pinning 2 (on request) 2.54 mm Pinning 2 (on request)

Available Pinnings

Туре	Transmitter	Receiver	
SBL52414x	2 (Standard)	1 (Standard)	
SBL51414x	1 (on request)	1 (on request)	

Other Pinnings on request /

different drawing set required for non standard pinning

EYE SAFETY

Ensure to avoid exposure of human eyes to high power laser diode emitted laser beams. Especially do not look directly into the laser diode or the collimated laser beam when the diode is activated.

CLASS 3B LASER PRODUCT according to IEC 60825-1

Required Labels



INVISIBLE LASER RADIATION AVOID EXPOSURE TO BEAM Class 3B Laser Product

Class IIIb LASER PRODUCT according to FDA Regulations complies with 21 CFR 1040.10 and 1040.11

Required Label



Laser Data

Wavelength	1310 nm
Maximum total output power	less than 50 mW
Beam divergence (1/e ²)	10°

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Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

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Information

For further information on technology, delivery terms and conditions and prices please contact the Infineon Technologies offices or our Infineon Technologies Representatives worldwide - see our webpage at

www.infineon.com/fiberoptics

CONNECTOR OPTIONS

Model	Туре
SBL52414G SBL51414G	SM FC/PC
SBL52414N SBL51414N	SM SC/PC 0°
SBL52414Z SBL51414Z	SM without connector

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your Infineon Technologies offices

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.